

# 2SB1216/2SD1816

# **High-Current Switching Applications**

### **Applications**

 Suitable for relay drivers, high-speed inverters, converters, and other general high-current switching applications.

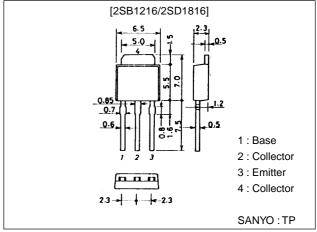
#### **Features**

- · Low collector-to-emitter saturation voltage.
- · Good linearity of hFF.
- · Small and slim package facilitating compactness of sets.
- · High f<sub>T</sub>.
- · Fast switching time.

## **Package Dimensions**

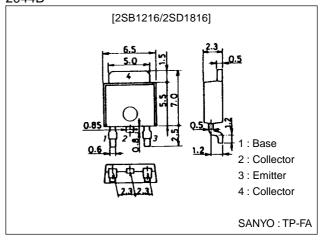
unit:mm

2045B



unit:mm

### 2044B



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#### ():2SB1216

# **Specifications**

## Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(–)120	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		(–)100	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(-)6	V
Collector Current	lc		(-)4	А
Collector Current (Pulse)	l <sub>CP</sub>		(-)8	А
Collector Dissipation	PC		1	W
		Tc=25°C	20	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

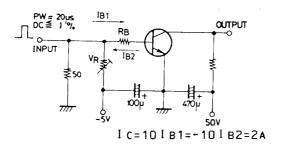
#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Unit		
Falametei	Symbol	Conditions	min	typ	max	Offic
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)100V, I <sub>E</sub> =0			(–)1	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =(-)4V, I <sub>C</sub> =0			(–)1	μΑ
DC Current Gain	h <sub>FE</sub> 1	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)0.5A	70*		400*	
	h <sub>FE</sub> 2	V <sub>CE</sub> =(-)5V, I <sub>C</sub> =(-)3A	40			
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)0.5A		(130)		MHz
				180		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)10V, f=1MHz		(65)40		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	I <sub>C</sub> =(-)2A, I <sub>B</sub> =(-)0.2A		150	400	mV
				(-200)	(-500)	mV
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)2A, I <sub>B</sub> =(-)0.2A		(-)0.9	(–)1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)10μA, I <sub>E</sub> =0	(–)120			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(–)100			V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =(-)10μA, I <sub>C</sub> =0	(–)6			V
Turn-ON Time	ton	See specified Test Circuit		100		ns
Storage Time	t <sub>stg</sub>	See specified Test Circuit		(800)		ns
				900		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit		50		ns

 $<sup>\</sup>ast$  : The 2SB1216/2SD1816 are classified by 0.5A  $h_{FE}$  as follows :

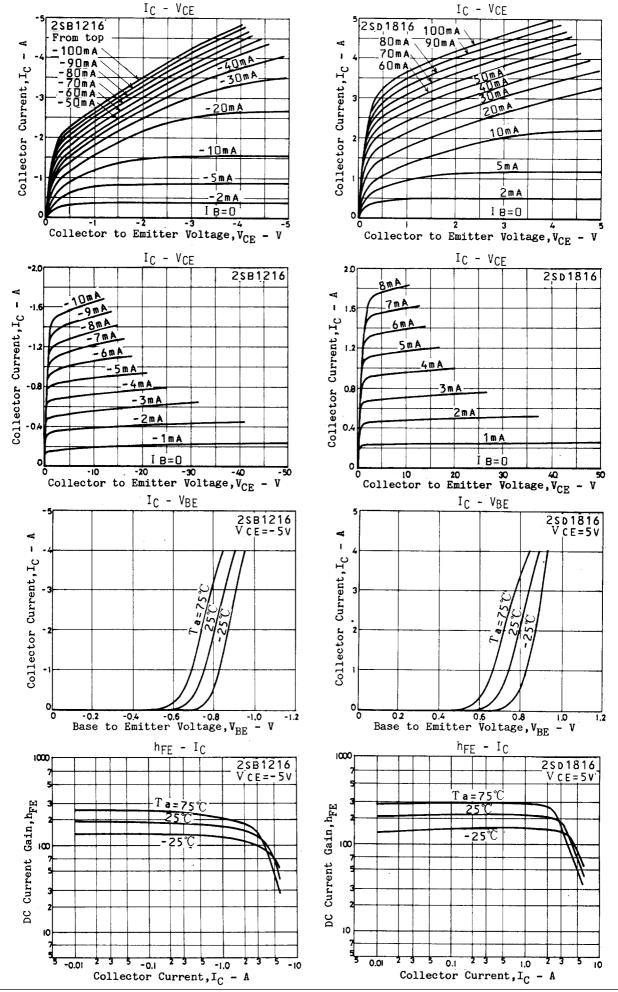
70	Q	140	100	R	200	140	S	280	200	Т	400
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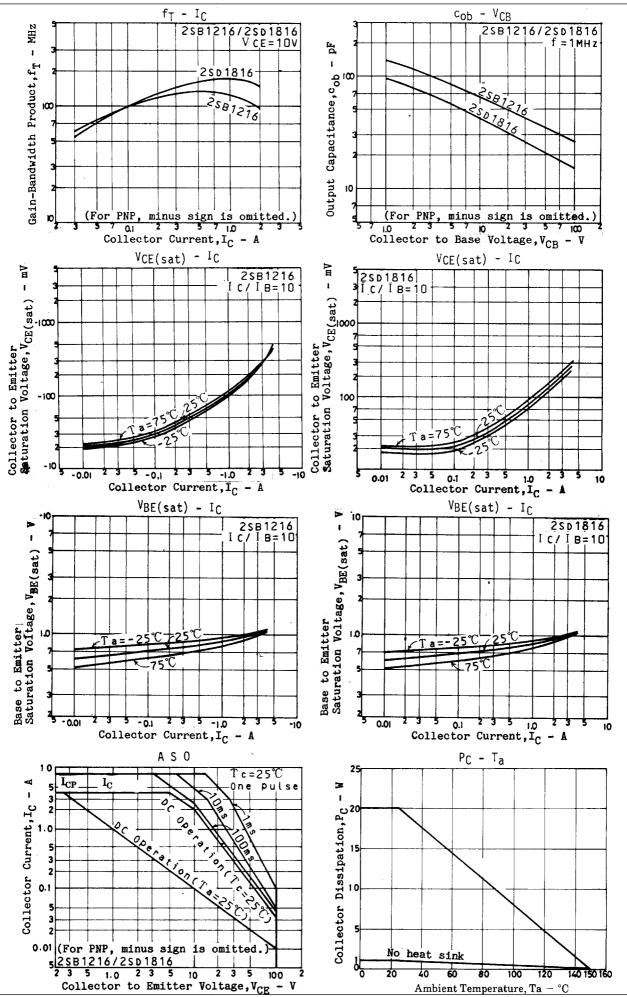
### **Switching Time Test Circuit**



(For PNP, minus sign is omitted.)
Unit (resistance: Ω, capacitance: F)

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